

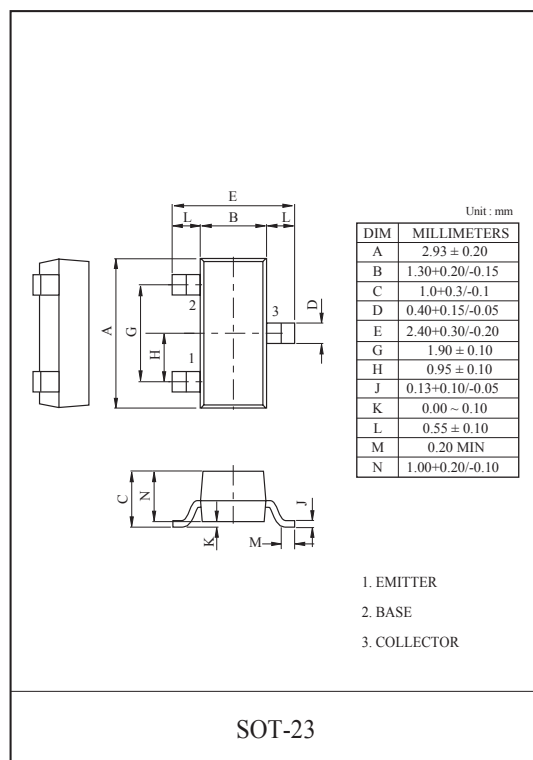
FOR MUTING AND SWITCHING APPLICATION.

FEATURES

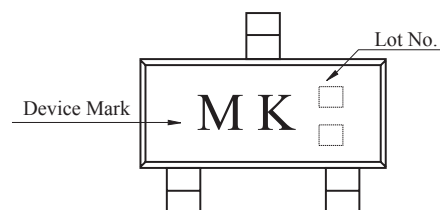
- High Emitter-Base Voltage : $V_{EBO}=25V(\text{Min.})$
- High Reverse h_{FE}
- Low on Resistance : $R_{ON}=0.86\Omega$ (Typ.), ($I_B=5mA$)
- Small collector to emitter saturation voltage
: $V_{CE(sat)} = 50mV(\text{Typ.})$

MAXIMUM RATING ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	25	V
Collector Current	I_C	300	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$



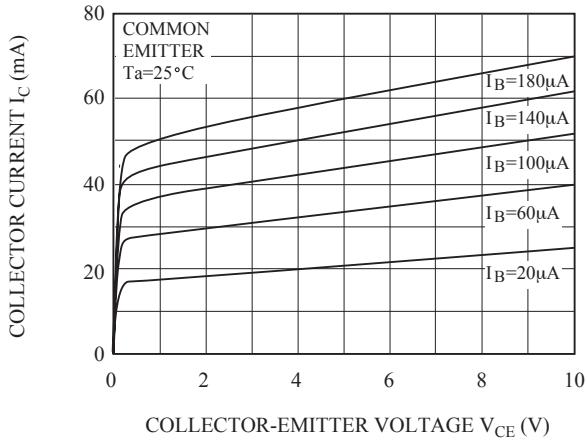
Marking

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

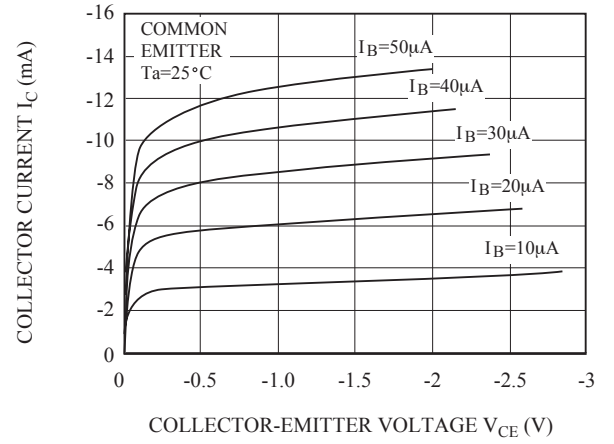
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A$	50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA$	20	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A$	25	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=25V, I_C=0$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=2V, I_C=4mA$	820	-	2700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=30mA, I_B=3mA$	-	50	100	mV
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	5.2	-	pF
Output on-Resistance	R_{ON}	$I_B=5mA, V_I=100mV_{(rms)}, f=1KHz, R_L=1k\Omega$	-	0.86	-	Ω

KTC2875AS

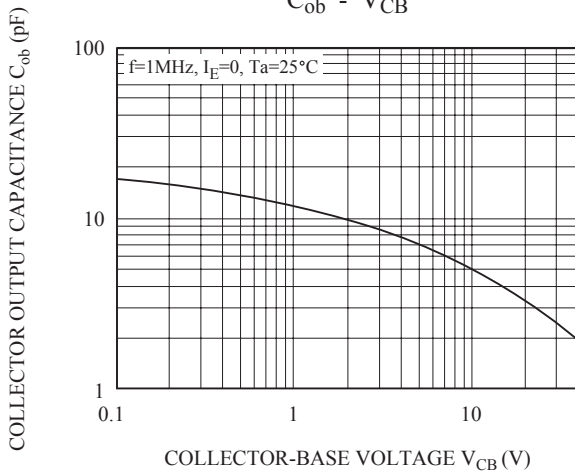
$I_C - V_{CE}$



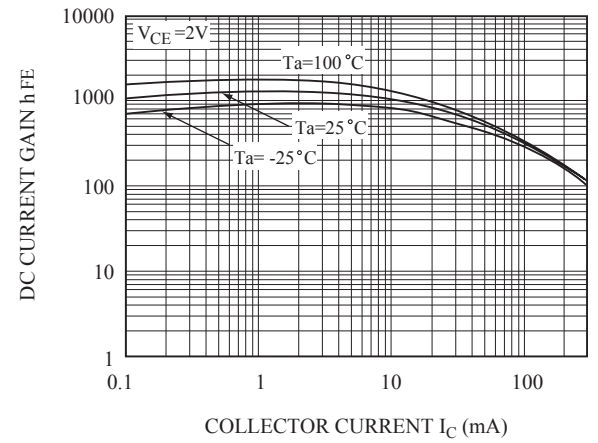
$I_C - V_{CE}$ (REVERSE REGION)



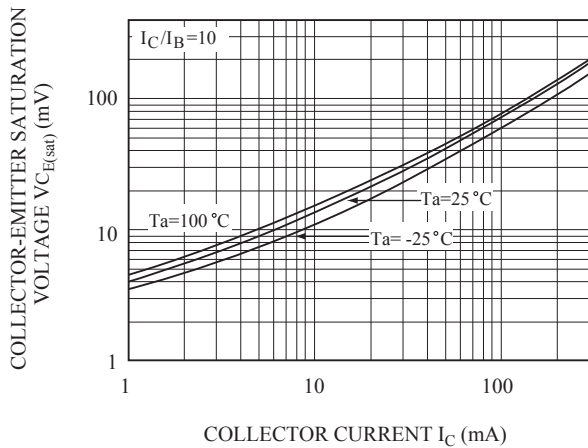
$C_{ob} - V_{CB}$



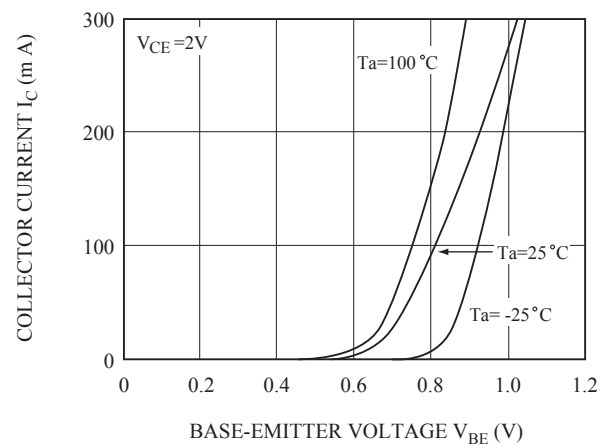
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



KTC2875AS

